TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS098

CD40107B Types

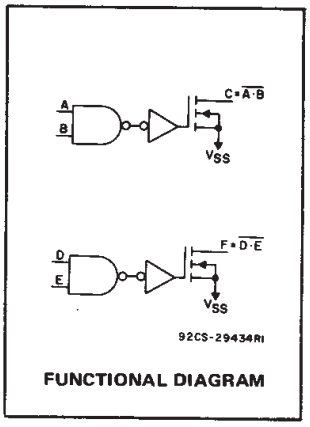
CMOS Dual 2-Input NAND Buffer/Driver

High-Voltage Type (20-Volt Rating)

■ CD40107B is a dual 2-input NAND buffer/driver containing two independent 2-input NAND buffers with open-drain single n-channel transistor outputs. This device features a wired-OR capability and high output sink current capability (136 mA typ. at V_{DD} = 10 V, V_{DS} = 1 V). The CD40107B is supplied in the 8-lead dual-in-line plastic (Mini-DIP) package (E suffix), 14-lead hermetic frit-seal ceramic package (F suffix), and in chip form (H suffix).

Features:

- **32 times standard B-Series output current drive sinking capability — 136 mA typ. @ V_{DD} = 10 V, V_{DS} = 1 V**
- **100% tested for quiescent current at 20 V**
- **Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C**
- **5-V, 10-V, and 15-V parametric ratings**
- **Noise margin, full package temperature range, R_L to V_{DD} = 10 kΩ:**
  1 V at V_{DD} = 5 V
  2 V at V_{DD} = 10 V
  2.5 V at V_{DD} = 15 V
- **Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"**



FUNCTIONAL DIAGRAM

Applications

- **Driving relays, lamps, LEDs**
- **Line driver**
- **Level shifter (up or down)**

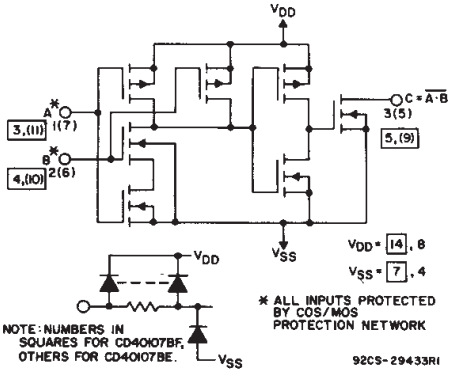


Fig.1 — Schematic diagram of CD40107B (one of 2 gates)

TRUTH TABLE

A	B	C	
0	0	1*	Z#
1	0	1*	Z#
0	1	1*	Z#
1	1	0	

*Requires external pull-up resistor (R_L) to V_{DD}.

#Without pull-up resistor (3-state).

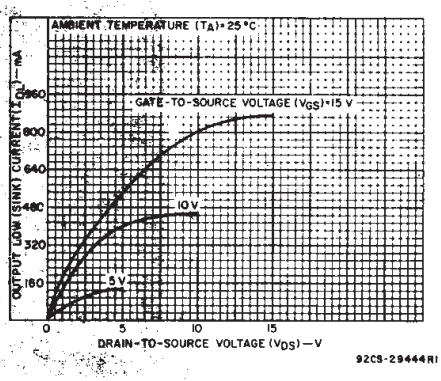


Fig.2 — Typical output low (sink) current characteristics.

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)..... 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

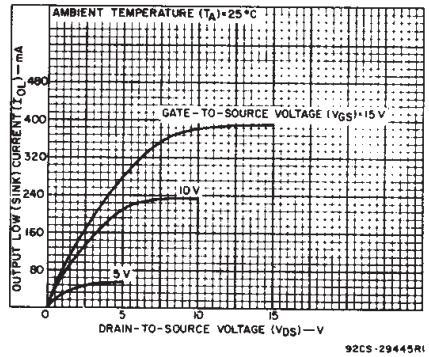


Fig.3 — Minimum output low (sink) current characteristics.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A= Full Package-Temperature Range)	3	18	V

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^oC$, $C_L = 50$ pF, Input $t_r, t_f = 20$ ns

CHARACTERISTIC	TEST CONDITIONS	V_{DD} Volts	LIMITS Typ.	LIMITS Max.	UNITS
Propagation Delay: High-to-Low, t_{PHL}	R_L* = 120 Ω	5	100	200	ns
		10	45	90	
		15	30	60	
Low-to-High, t_{PLH}	R_L* = 120 Ω	5	100	200	ns
		10	60	120	
		15	50	100	
Transition Time: High-to-Low, t_{THL}	R_L* = 120 Ω	5	50	100	ns
		10	20	40	
		15	10	20	
Low-to-High, t_{TLH}	R_L* = 120 Ω	5	50	100	ns
		10	35	70	
		15	25	50	
Average Input Capacitance, C_{IN}	Any Input		5	7.5	pF
Average Output Capacitance, C_{OUT}	Any Output		30	–	pF

* R_L is external pull-up resistor to V_{DD}.

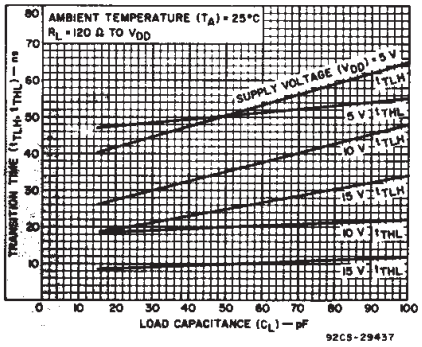


Fig.4 – Typical transition time as a function of load capacitance.

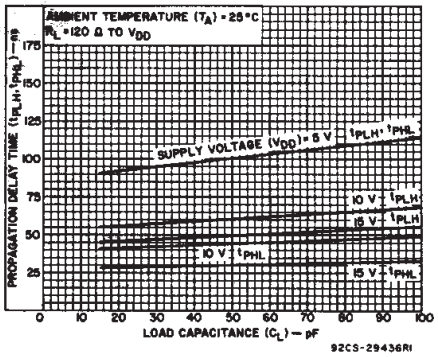


Fig.5 – Typical propagation delay time as a function of load capacitance.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	V_O (V)	V_{IN} (V)	V_{DD} (V)	LIMITS AT INDICATED TEMPERATURES (°C) –55	–40	+85	+125	+25 Min.	+25 Typ.	+25 Max.	UNITS
Quiescent Device Current I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	21	20	14	12	16	32	–	mA
	1	0,5	5	44	42	30	25	34	68	–	
	0.5	0,10	10	49	46	32	28	37	74	–	
	1	0,10	10	89	85	60	51	68	136	–	
	0.5	0,15	15	66	63	44	38	50	100	–	
Output High (Source) Current I_{OH} Min.	No Internal Pull-Up Device										
Input Low Voltage V_{IL} Max.*	4.5	–	5	1.5				–	–	1.5	V
	9	–	10	3				–	–	3	
	13.5	–	15	4				–	–	4	
Input High Voltage V_{IH} Min.*	0.5,4.5	–	5	3.5				3.5	–	–	
	1,9	–	10	7				7	–	–	
	1.5,13.5	–	15	11				11	–	–	
Input Current I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$±10^{-5}$	±0.1	μA
Output Leakage Current I_{OZ} Max.	18	0,18	18	2	2	20	20	–	10^{-4}	2	μA

* Measured with external pull-up resistor, R_L = 10 kΩ to V_{DD}.

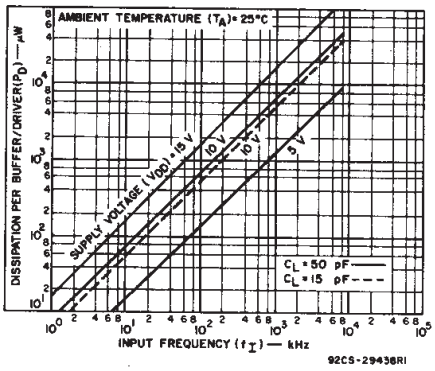


Fig.6 – Typical power dissipation as a function of input frequency.

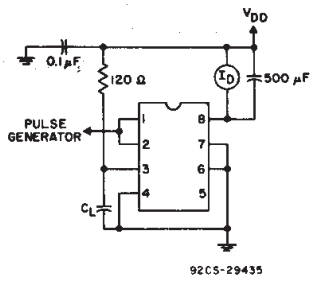
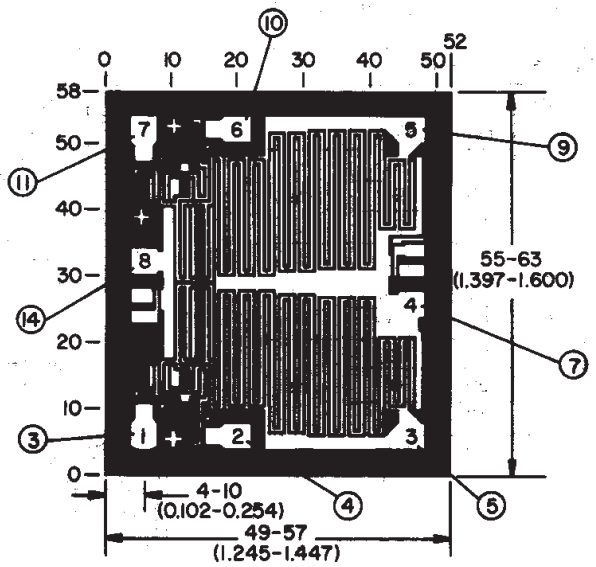


Fig. 7 – Power-dissipation test circuit for CD40107BE.



NOTE: NOS. IN PADS FOR CD40107BE
NOS. OUTSIDE CHIP FOR CD40107BF

Dimensions and Pad Layout for CD40107BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

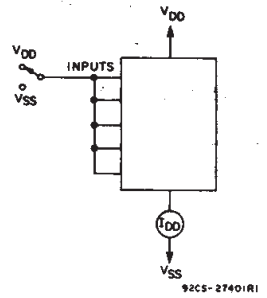


Fig.8 – Quiescent-device current test circuit.

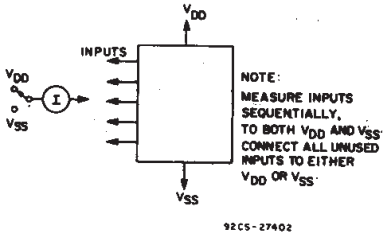


Fig. 9 – Input-current test circuit.

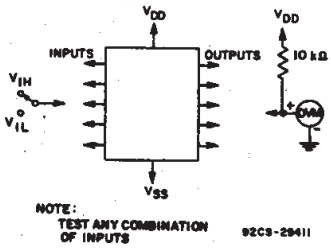
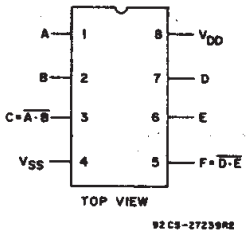
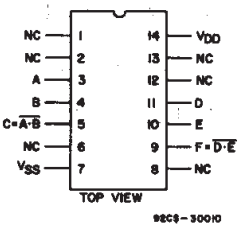


Fig.10 – Input-voltage test circuit.



CD40107BE



CD40107BF

TERMINAL ASSIGNMENTS

Special Considerations for CD40107B

1. **Limiting Capacitive Currents for CL > 500 pF, V_{DD} > 15 V.**
   For V_{DD} > 15 V, and load capacitance (C_L) from output to ground > 500 pF, an external 25 Ω series limiting resistor should be inserted between the output terminal and C_L. No external resistor is necessary if C_L < 500 pF or V_{DD} < 15 V.
2. **Driving Inductive Loads**
   When using the CD40107B to drive inductive loads, the load should be shunted with a diode to prevent high voltages from developing across the CD40107B output.

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